# onsemi

# **ESD Protection Diode**

### Micro-Packaged Diodes for ESD Protection

## ESD7481, SZESD7481

The ESD7481 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, the part is well suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

#### Features

- Ultra-Low Capacitance 0.25 pF
- Low Clamping Voltage
- Small Body Outline Dimensions: 0.60 mm x 0.30 mm
- Low Body Height: 0.3 mm
- Stand-off Voltage: 3.3 V
- Low Leakage
- Insertion Loss: 0.030 dBm
- Response Time is < 1 ns
- Low Dynamic Resistance < 1  $\Omega$
- IEC61000-4-2 Level 4 ESD Protection
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

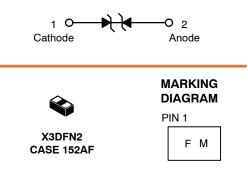
- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications

#### MAXIMUM RATINGS

| Rating   | Symbol                             | Value       | Unit       |
|--|------------------------------------|-------------|------------|
| IEC 61000-4-2 (ESD) Contact<br>Air   |                                    | ±20<br>±20  | kV         |
| Total Power Dissipation on FR–5 Board<br>(Note 1) @ $T_A = 25^{\circ}C$<br>Thermal Resistance, Junction–to–Ambient | Ρ <sub>D</sub><br>R <sub>θJA</sub> | 250<br>400  | mW<br>°C/W |
| Junction and Storage Temperature Range   | T <sub>J</sub> , T <sub>stg</sub>  | -40 to +125 | °C         |
| Lead Solder Temperature – Maximum (10 Second Duration)   | ΤL                                 | 260         | °C         |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. FR-5 =  $1.0 \times 0.75 \times 0.62$  in.

See Application Note AND8308/D for further description of survivability specs.



F = Specific Device Code

M = Date Code

#### **ORDERING INFORMATION**

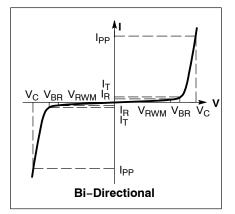
| Device         | Package             | Shipping <sup>†</sup>  |
|----------------|---------------------|------------------------|
| ESD7481MUT5G   | X3DFN2<br>(Pb–Free) | 10000 / Tape &<br>Reel |
| SZESD7481MUT5G | X3DFN2<br>(Pb-Free) | 15000 / Tape &<br>Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> =  $25^{\circ}$ C unless otherwise noted)

| Symbol           | Parameter  |  |  |
|------------------|--|--|--|
| I <sub>PP</sub>  | Maximum Reverse Peak Pulse Current                 |  |  |
| V <sub>C</sub>   | Clamping Voltage @ IPP                             |  |  |
| V <sub>RWM</sub> | Working Peak Reverse Voltage                       |  |  |
| I <sub>R</sub>   | Maximum Reverse Leakage Current @ V <sub>RWM</sub> |  |  |
| V <sub>BR</sub>  | Breakdown Voltage @ I <sub>T</sub>                 |  |  |
| Ι <sub>Τ</sub>   | Test Current                                       |  |  |



| *See Application Note AND8308/D for detailed explanations of |  |
|--|--|
| datasheet parameters.  |  |

| Parameter                  | Symbol           | Conditions   | Min                 | Тур            | Max          | Unit |
|----------------------------|------------------|--|---------------------|----------------|--------------|------|
| Reverse Working Voltage    | V <sub>RWM</sub> |  |                     |                | 3.3          | V    |
| Breakdown Voltage (Note 2) | V <sub>BR</sub>  | I <sub>T</sub> = 1 mA                              |                     | 6.0            |              | V    |
| Reverse Leakage Current    | I <sub>R</sub>   | V <sub>RWM</sub> = 3.3 V                           |                     | < 1.0          | 50           | nA   |
| Clamping Voltage (Note 3)  | V <sub>C</sub>   | I <sub>PP</sub> = 1 A                              |                     |                | 10           | V    |
| Clamping Voltage (Note 3)  | V <sub>C</sub>   | I <sub>PP</sub> = 3 A                              |                     |                | 12           | V    |
| ESD Clamping Voltage       | V <sub>C</sub>   | Per IEC61000-4-2                                   | See Figures 1 and 2 |                |              |      |
| Junction Capacitance       | CJ               | $V_R = 0 V$ , f = 1 Mhz<br>$V_R = 0 V$ , f < 1 GHz |                     | 0.25<br>0.15   | 0.40<br>0.30 | pF   |
| Dynamic Resistance         | R <sub>DYN</sub> | TLP Pulse  |                     | 0.60           |              | Ω    |
| Insertion Loss             |                  | f = 1 Mhz<br>f = 8.5 GHz                           |                     | 0.030<br>0.234 |              | dB   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.

3. Non-repetitive current pulse at T<sub>A</sub> = 25°C, per IEC61000-4-5 waveform.



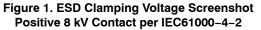
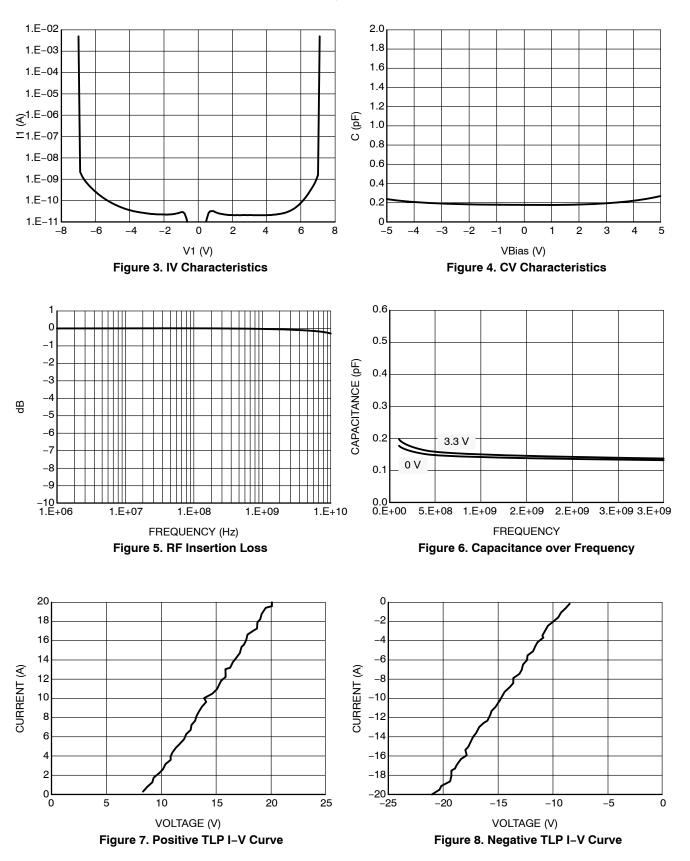




Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

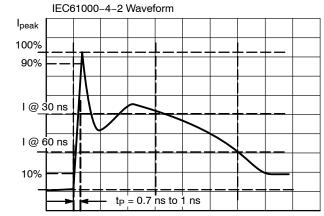
### ESD7481, SZESD7481



#### ESD7481, SZESD7481

#### IEC 61000-4-2 Spec.

| Level | Test Volt-<br>age (kV) | First Peak<br>Current<br>(A) | Current at<br>30 ns (A) | Current at<br>60 ns (A) |
|-------|------------------------|------------------------------|-------------------------|-------------------------|
| 1     | 2                      | 7.5                          | 4                       | 2                       |
| 2     | 4                      | 15                           | 8                       | 4                       |
| 3     | 6                      | 22.5                         | 12                      | 6                       |
| 4     | 8                      | 30                           | 16                      | 8                       |





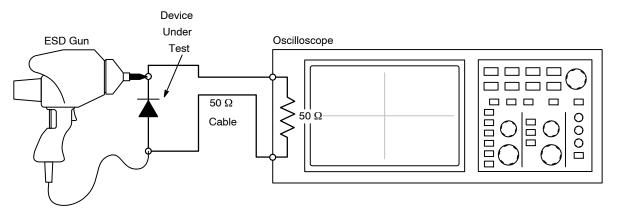


Figure 10. Diagram of ESD Test Setup

#### **ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. onsemi has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how onsemi creates these screenshots and how to interpret them please refer to AND8307/D.

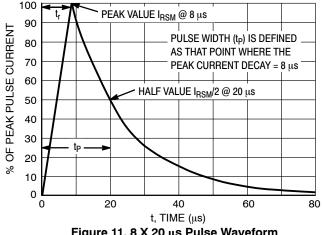
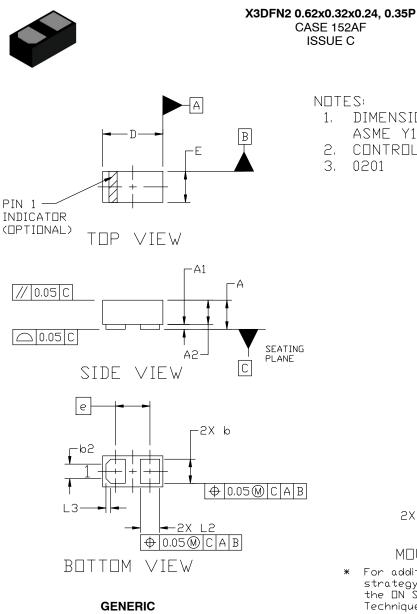
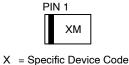


Figure 11. 8 X 20 µs Pulse Waveform





### MARKING DIAGRAM\*



M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

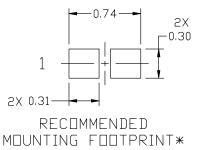
| DOCUMENT NUMBER: | 98AON56472E Electronic versions are uncontrolled except when accessed directly from the Document Repository.   Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |  |             |
|------------------|--|--|-------------|
| DESCRIPTION:     | X3DFN2 0.62x0.32x0.24, 0.35P   |  | PAGE 1 OF 1 |
|                  |  |  |             |

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- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION MILLIMETERS

| r   | 1           |      |      |  |
|-----|-------------|------|------|--|
|     | MILLIMETERS |      |      |  |
| DIM | MIN,        | NDM. | MAX. |  |
| А   | 0.25        | 0.29 | 0.33 |  |
| A1  | 0.00        |      | 0.05 |  |
| A2  | 0.14        | 0.24 | 0.34 |  |
| b   | 0.22        | 0.25 | 0.28 |  |
| b2  | 0.150 REF   |      |      |  |
| D   | 0.58        | 0.62 | 0.66 |  |
| E   | 0.28        | 0.32 | 0.36 |  |
| e   | 0.355 BSC   |      |      |  |
| L2  | 0.17        | 0.20 | 0.23 |  |
| L3  | 0.050 REF   |      |      |  |



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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